NT511740D0J

DATA SHEET

Contents

DESCRIPTION

This is a family of 4,194,304 x 4 bit Fast Page Mode CMOS DRAMs. Fast Page Mode offers high speed random access of memory cells within the same row. Power supply voltage (+5.0V), refresh cycle (2K Ref), access time (-5 or -6), power consumption (Normal or Low power) and package type (SOJ) are optional features of this family.

All of this family have $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh, $\overline{\text{RAS}}$-only refresh and Hidden refresh capabilities. Furthermore, Self-refresh operation is available in L-version. This 4Mx4 EDO Mode DRAM family is fabricated using NANYA's advanced CMOS process to realize high bandwidth, low power consumption and high reliability.

It may be used as main memory unit for microcomputer, high level computer and personal computer .

FEATURES

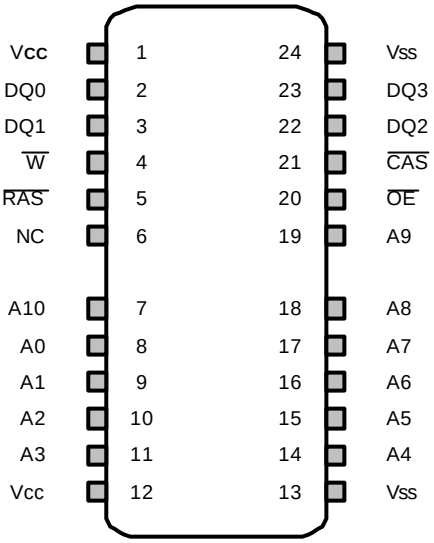
- Fast Page Mode operation .
- TTL(5V) compatible inputs and outputs
- Single +5V ± 10% power supply
- JEDEC Standard pinout
- $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, hidden refresh, $\overline{\text{RAS}}$-only refresh capability
- Refresh : 2048 cycles / 32 ms
- Self-refresh capability (L-ver only)
- Multi-bit test mode capability
- Available in plastic SOJ packages

PRODUCT FAMILY

Family	Access Time (Max.)				Active Power Dissipation	Voltage	Package
	tRAC	tCAC	tRC	tPC			
NT511740D0J - 50/5L	50ns	13ns	90ns	35ns	605mW	5V	26(24)-pin SOJ
NT511740D0J - 60/6L	60ns	15ns	110ns	40ns	550mW		

PIN CONFIGURATION (TOP VIEW)

NT511740D0J



300mil 26(24)-pin SOJ

Pin Name	Pin Function
A0-A10	Address Inputs
DQ0-DQ3	Data Input / Output
Vss	Ground
$\overline{RAS}$	Row Address Strob
$\overline{CAS}$	Column Address Strob
$\overline{W}$	Read/Write Input
$\overline{OE}$	Data Output Enable
Vcc	Power +5.0 V (+ 3.3V)
NC	No Connection

ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Voltage on Any Pin Relative to V_{SS}	V_{IN},V_{OUT}	-1.0 to +7.0	V
Voltage on V_{CC} Supply Relative to V_{SS}	V_{CC}	-1.0 to +7.0	V
Short Circuit Output Current	I_{OS}	50	mA
Power Dissipation	P_D*	1	W
Operation Temperature	T_{opr}	0 to 70	°C
Storage Temperature	T_{stg}	-55 to 150	°C

*:Ta = 25°C

- Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

(Voltage referenced to Vss, Ta = 0 °C to 70°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Ground	V_{SS}	0	0	0	V
Input High Voltage	V_{IH}	2.4	-	Vcc+1.0*1	V
Input Low Voltage	V_{IL}	-1.0*2	-	0.8	V

*1 : V_{cc} +2.0V/20ns(5V), Pulse width is measured at V_{cc}
*2 : -2.0V/20ns(5V), Pulse width is measured at V_{ss}

Capacitance

(Vcc = 5V, Ta = 25°C, f = 1 MHZ)

Parameter	Symbol	Typ.	Max.	Unit
Input Capacitance (A0 -A11)	C_{IN1}	-	5	pF
Input Capacitance ($\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$)	C_{IN2}	-	7	pF
Output Capacitance (DQ0-DQ3)	$C_{I/O}$	-	7	pF

DC Characteristics

(Recommended operating conditions unless otherwise noted.)

Max	Parameter	Symbol	Min	Max	Units
5V	Input Leakage Current (Any input 0 <= V_{IN} <= V_{IN}+0.5V, all other input pins not under test =0 Volt)	II(L)	-5	5	uA
	Output Leakage Current (Data out is disabled, 0 <= V_{OUT} <= V_{CC})	IO(L)	-5	5	uA
	Output High Voltage Level (I_{OH}= -5mA)	V_{OH}	2.4	-	V
	Output Low Voltage Level (I_{OL}=4.2mA)	V_{OL}	-	0.4	V

DC CHARACTERISTICS (Continued)

Symbol	Power	Speed	Max	Units
ICC1	Don't care	-5	110	mA
		-6	100	mA
ICC2	Normal	Don't care	2	mA
	L		1	mA
ICC3	Don't care	-5	110	mA
		-6	100	mA
ICC4	Don't care	-5	90	mA
		-6	80	mA
ICC5	Normal	Don't care	3	mA
	L		200	uA
ICC6	Don't care	-5	110	mA
		-6	100	mA
ICC7	L	Don't care	300	uA
ICCS	L	Don't care	250	uA

ICC1* : Operating Current ($\overline{RAS}$ and $\overline{CAS}$ cycling @ t_{RC}=min.)

ICC2 : Standby Current ($\overline{RAS}$ = $\overline{CAS}$ = $\overline{W}$ =V_{IH})

ICC3* : $\overline{RAS}$-only Refresh Current ($\overline{RAS}$=V_{IH}, $\overline{RAS}$ cycling @ t_{RC}=min.)

ICC4* : Fast Page Mode Current ($\overline{RAS}$=V_{IL}, $\overline{CAS}$ Address cycling @ tPC=min.)

ICC5 : Standby Current ($\overline{RAS}$ = $\overline{CAS}$ = $\overline{W}$ =V_{CC}-0.2V)

ICC6* : CAS-Before-$\overline{RAS}$ Refresh Current ($\overline{RAS}$, $\overline{CAS}$ cycling @ t_{RC}=min.)

ICC7 : Battery back-up current, Average power supply current, Battery back-up mode Input high voltage (V_{IH})=VCC-0.2V, Input low voltage (V_{IL})=0.2V, $\overline{CAS}$ =0.2V, DQ=Don' t care, t_{RC}=125us(2K/L-ver) , t_{RAS}=t_{RAS}min~300ns

ICCS : Self Refresh Current
($\overline{RAS}$ = $\overline{CAS}$ =0.2V, $\overline{W}$ = $\overline{OE}$ =A0 ~ A11=VCC-0.2V or 0.2V, DQ0 ~ DQ3=VCC-0.2V, 0.2V or open)

*Note : ICC1, ICC3, ICC4 and ICC6 are dependent on output loading and cycle rates. Specified values are obtained with the output open. ICC is specified as an average current. In ICC1, ICC3 and ICC6, address can be changed maximum once while $\overline{RAS}$=V_{IL}. In ICC4, address can be changed maximum once within one Fast Page Mode cycle time, tPC.

AC CHARACTERISTICS

(0°C ≤ Ta ≤ 70°C , See note 1,2) ; Test condition : VCC=5.0V ± 10%, V_{IH}/V_{IL}=2.4/0.8V, V_{OH}/V_{OL}=2.0/0.8V

Parameter	Symbol	-50		-60		Unit	Notes
		Min	Max	Min	Max		
Random read or write cycle time	t RC	90	-	110	-	ns	
Read-modify-write cycle time	t RWC	131		155		ns	
Access time from $\overline{RAS}$	t RAC		50		60	ns	3,4,10
Access time from $\overline{CAS}$	t CAC		13		15	ns	3,4,5
Access time from column address	t AA		25		30	ns	3,10
$\overline{CAS}$ to output in Low-Z	t CLZ	0		0		ns	3
Output buffer turn-off delay	t OFF	0	13	0	15	ns	6
Transition time (rise and fall)	t T	3		3		ns	2
$\overline{RAS}$ precharge time	t RP	30		40		ns	
$\overline{RAS}$ pulse width	t RAS	50		60		ns	
$\overline{RAS}$ hold time	t RSH	13		15		ns	
$\overline{CAS}$ hold time	t CSH	50		60		ns	
$\overline{CAS}$ pulse width	t CAS	13		15		ns	
$\overline{RAS}$ to $\overline{CAS}$ delay time	t RCD	17	37	20	45	ns	4
$\overline{RAS}$ to column address delay time	t RAD	12		15		ns	10
$\overline{CAS}$ to $\overline{RAS}$ precharge time	t CRP	5		5		ns	
Row address set-up time	t ASR	0		0		ns	
Row address hold time	t RAH	7		10		ns	
Column address set-up time	t ASC	0		0		ns	
Column address hold time	t CAH	7		10		ns	
Column address to $\overline{RAS}$ lead time	t RAL	25		30		ns	
Read command set-up time	t RCS	0		0		ns	
Read command hold time referenced to $\overline{CAS}$	t RCH	0		0		ns	8
Read command hold time referenced to $\overline{RAS}$	t RRH	0		0		ns	8
Write command hold time	t WCH	7		10		ns	
Write command pulse width	t WP	7		10		ns	
Write command to $\overline{RAS}$ lead time	t RWL	13		15		ns	
Write command to $\overline{CAS}$ lead time	t CWL	7		10		ns	
Data set-up time	t DS	0		0		ns	9
Data hold time	t DH	7		10		ns	9
Refresh period (2K, Normal)	t REF		32		32	ms	
Refresh period (L-ver)	t REF		128		128	ms	
Write command set-up time	t WCS	0		0		ns	7

AC CHARACTERISTICS (Continued)

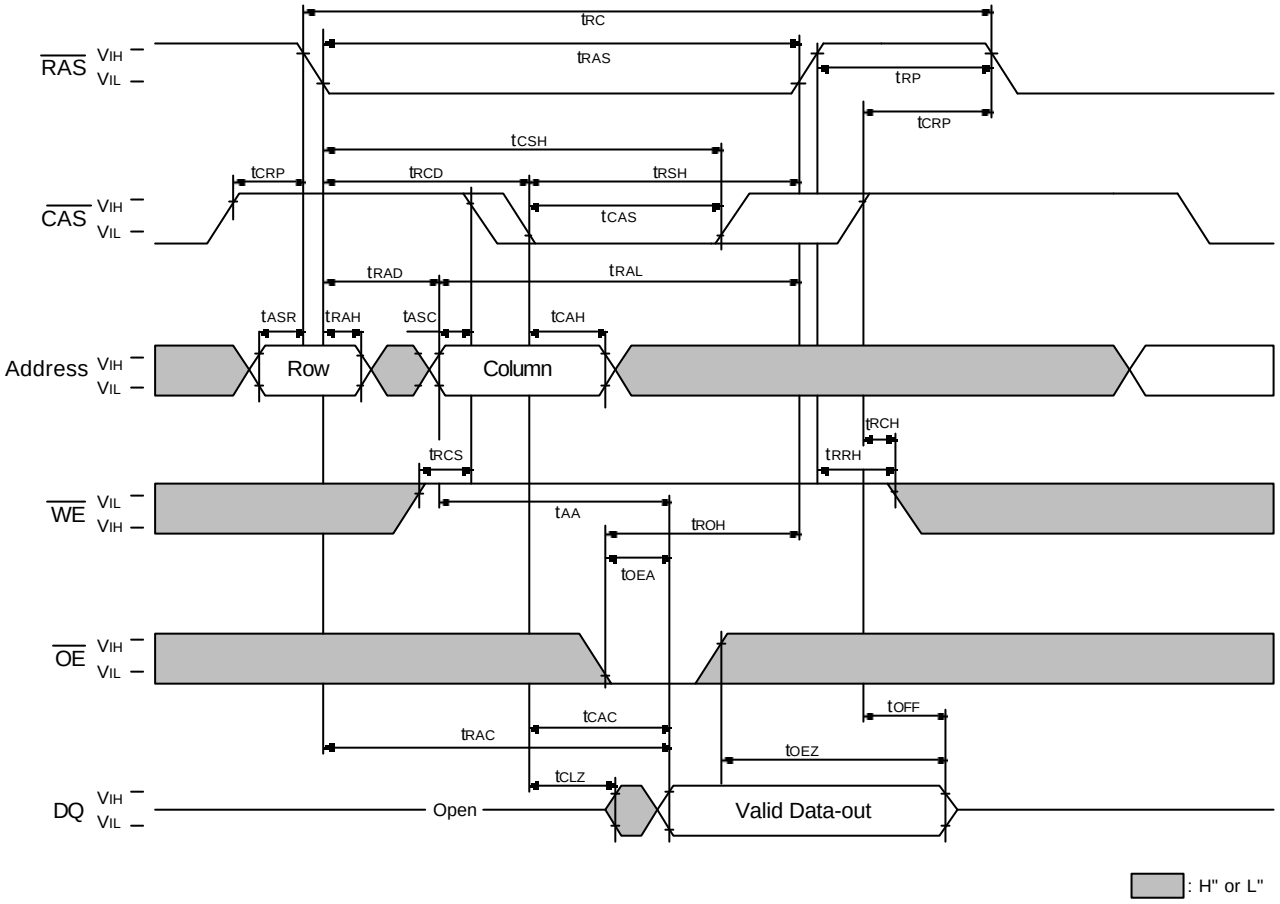
Parameter	Symbol	-50		-60		Unit	Notes
		Min	Max	Min	Max		
$\overline{CAS}$ to $\overline{W}$ delay time	t CWD	36		40		ns	7
$\overline{RAS}$ to $\overline{W}$ delay time	t RWD	73		85		ns	7
Column address to $\overline{W}$ delay time	t AWD	48		55		ns	7
$\overline{CAS}$ precharge to $\overline{W}$ delay time	t CPWD	53		60		ns	
$\overline{CAS}$ set-up time ($\overline{CAS}$ -before- $\overline{RAS}$ refresh)	t CSR	5		5		ns	
$\overline{CAS}$ hold time ($\overline{CAS}$ -before- $\overline{RAS}$ refresh)	t CHR	10		10		ns	
$\overline{RAS}$ to CAS precharge time	t RPC	5		5		ns	
Access time from $\overline{CAS}$ precharge	t CPA		30		35	ns	3
Hyper Page cycle time	t PC	35		40		ns	
Hyper Page read-modify-write cycle time	t PRWC	76		85		ns	
$\overline{CAS}$ precharge time (Hyper Page cycle)	t CP	7		10		ns	
$\overline{RAS}$ pulse width (Hyper Page cycle)	t RASP	50	100k	60	100k	ns	
$\overline{RAS}$ hold time from $\overline{CAS}$ precharge	t RHCP	30		35		ns	
$\overline{OE}$ access time	t OEA		13		15	ns	
$\overline{OE}$ to data delay	t OED	13		15		ns	
Output buffer turn off delay time from $\overline{OE}$	t OEZ	0	13	0	15	ns	6
$\overline{OE}$ command hold time	t OEH	13		15		ns	
$\overline{W}$ to $\overline{RAS}$ precharge time(C-B-R refresh)	t WRP	10		10		ns	
$\overline{W}$ to $\overline{RAS}$ hold time(C-B-R refresh)	t WRH	10		10		ns	
$\overline{RAS}$ pulse width (C-B-R self refresh)	t RASS	100		100		ns	11,12,13
$\overline{RAS}$ precharge time (C-B-R self refresh)	t RPS	90		110		ns	11,12,13
$\overline{CAS}$ hold time (C-B-R self refresh)	t CHS	-50		-50		ns	11,12,13

NOTES

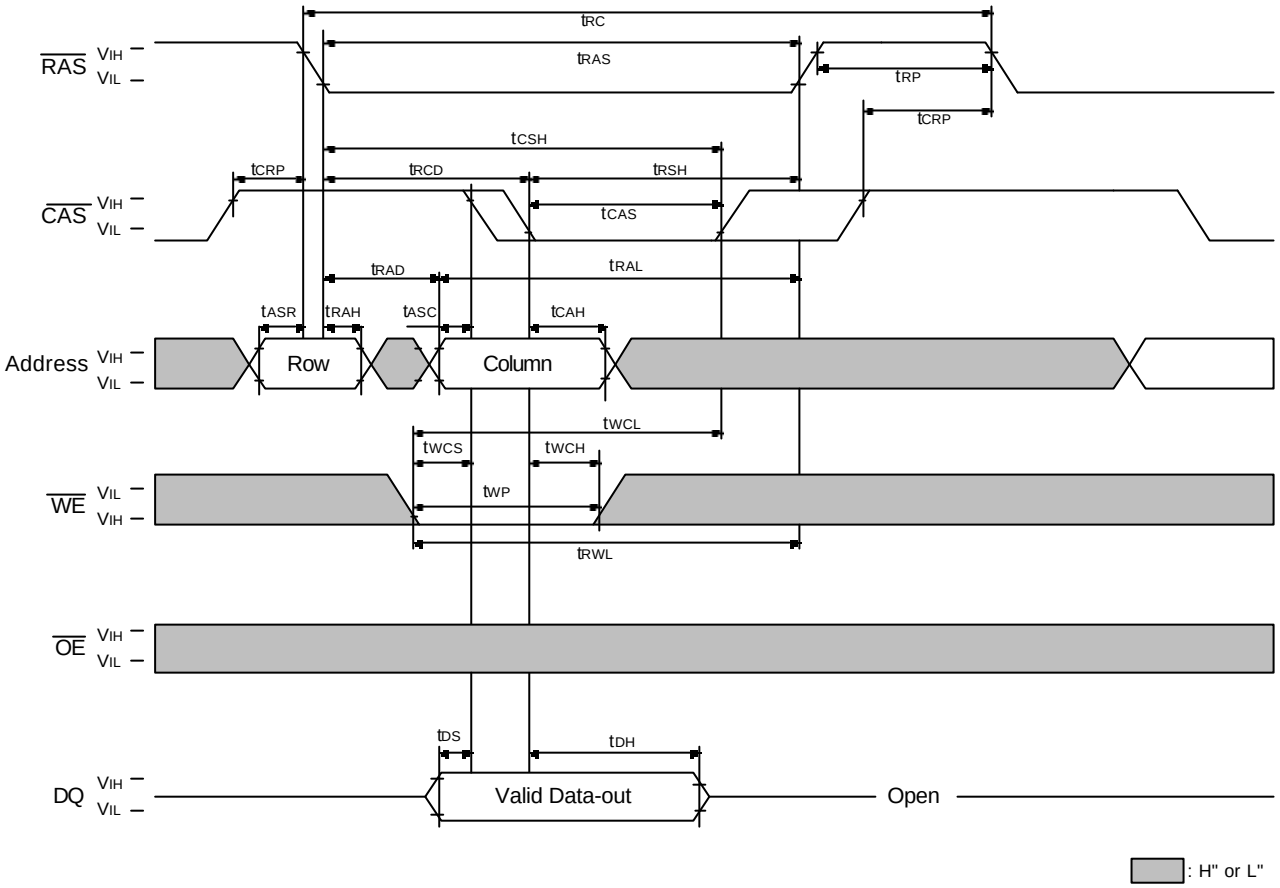
1. An initial pause of 200us is required after power-up followed by any 8 $\overline{RAS}$-only refresh or $\overline{CAS}$-before-$\overline{RAS}$ refresh Cycles before proper device operation is achieved.
2. V_{IH}(min) and V_{IL} (max) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} (min) and V_{IL} (max) and are assumed to be 5ns for all inputs.
3. Measured with a load equivalent to 2 TTL(5V) loads and 100pF.
4. Operation within the t RCD(max) limit insures that tRAC(max) can be met. tRCD(max) is specified as a reference point only. If tRCD is greater than the specified tRCD (max) limit, then access time is controlled exclusively by tCAC.
5. Assumes that tRCD >= tRCD(max).
6. tOFF(min) and tOEZ(max) define the time at which the output achieves the open circuit condition and is not referenced to V_{OH} or V_{OL}.
7. tWCS, tRWD, tCWD and tAWD are non restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If tWCS >= tWCS(min), the cycle is an early write cycle and the data output will remain high impedance for the duration of the cycle. If tCWD >= tCWD(min), tRWD >= tRWD(min) and tAWD >= tAWD(min), then the cycle is a read-modify-write cycle and the data output will contain the data read from the selected address. If neither of the above conditions is satisfied, the condition of the data out is indeterminate.
8. Either tRCH or tRRH must be satisfied for a read cycle.
9. These parameters are referenced to $\overline{CAS}$ falling edge in early write cycles and to $\overline{W}$ falling edge in read-modify-write controlled write cycles.
10. Operation within the tRAD (max) limit insures that tRAD(max) can be met. tRAD(max) is specified as a reference point only. If tRAD is greater than the specified tRAD(max) limit, then access time is controlled by tAA .
11. If tRASS >= 100us, then $\overline{RAS}$ precharge time must use tRPS instead of tRP.
12. For RAS-only refresh and burst $\overline{CAS}$-before-$\overline{RAS}$ refresh mode, 2048(2K) cycles of burst refresh must be executed within 32ms before and after self refresh, in order to meet refresh specification..
13. For distributed $\overline{CAS}$-before-$\overline{RAS}$ with 15.6us interval $\overline{CAS}$-before-$\overline{RAS}$ refresh should be executed with in 15.6us immediately before and after self refresh in order to meet refresh specification.

Timing Waveform

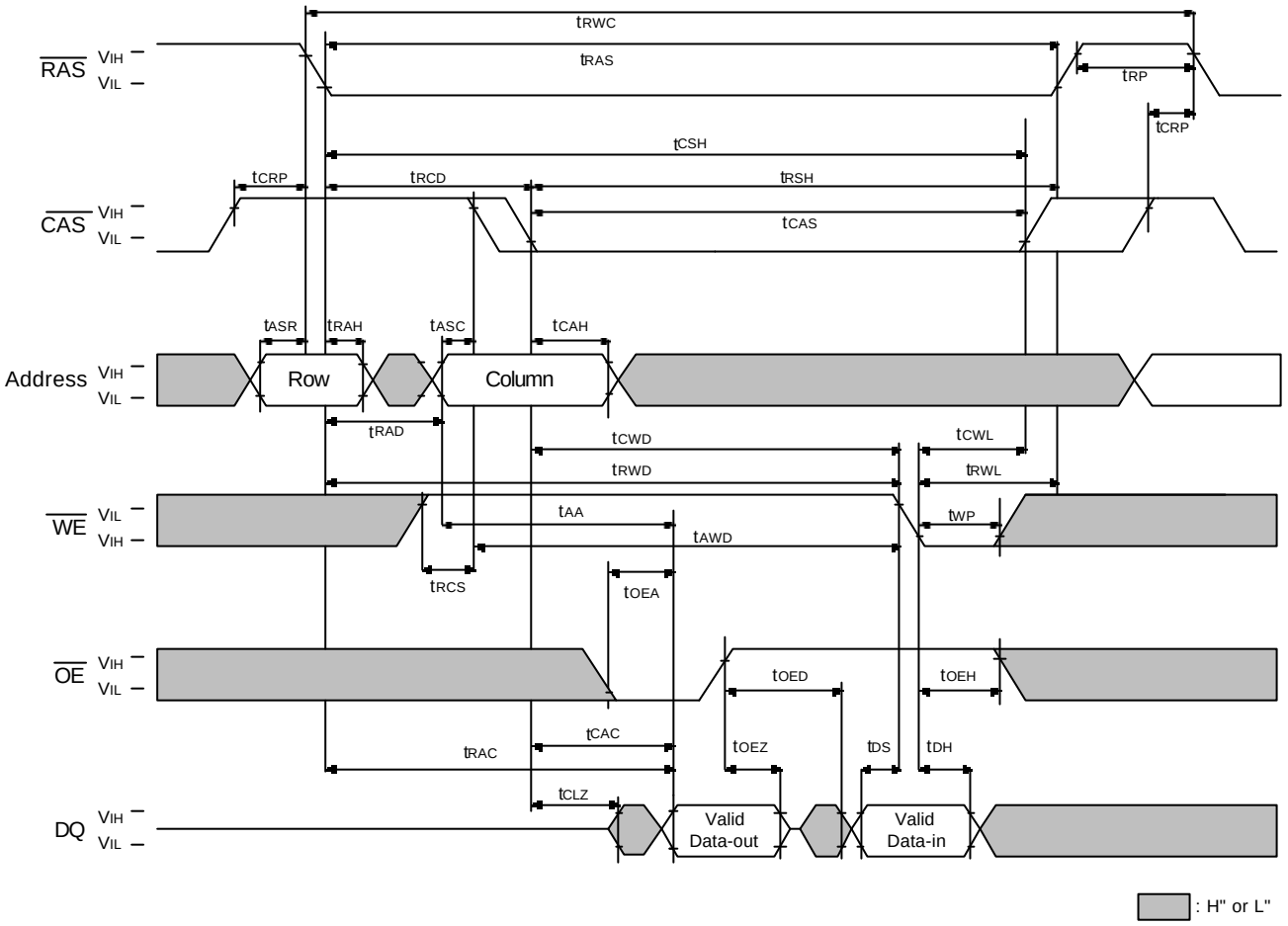
Read Cycle



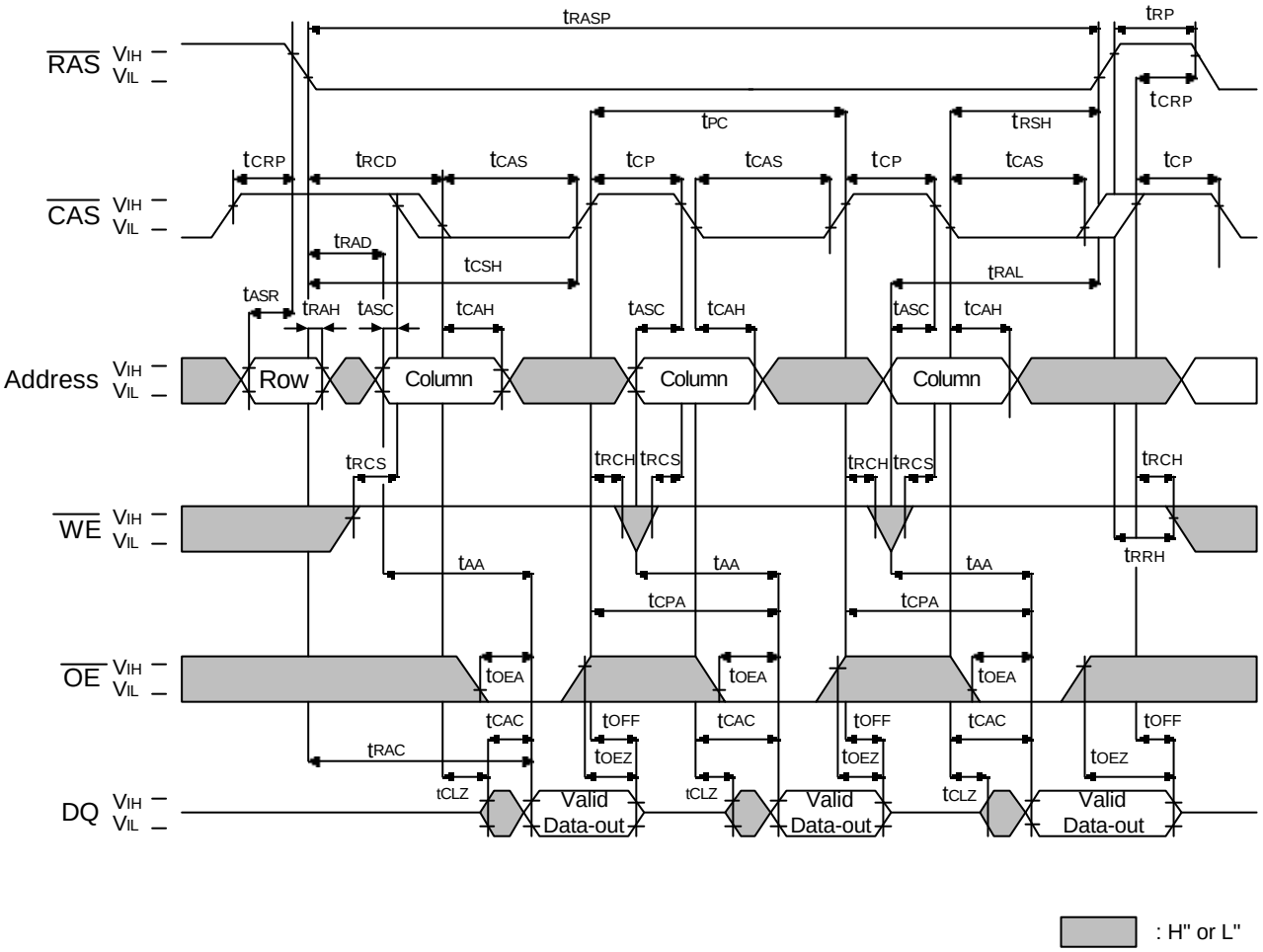
Write Cycle (Early Write)



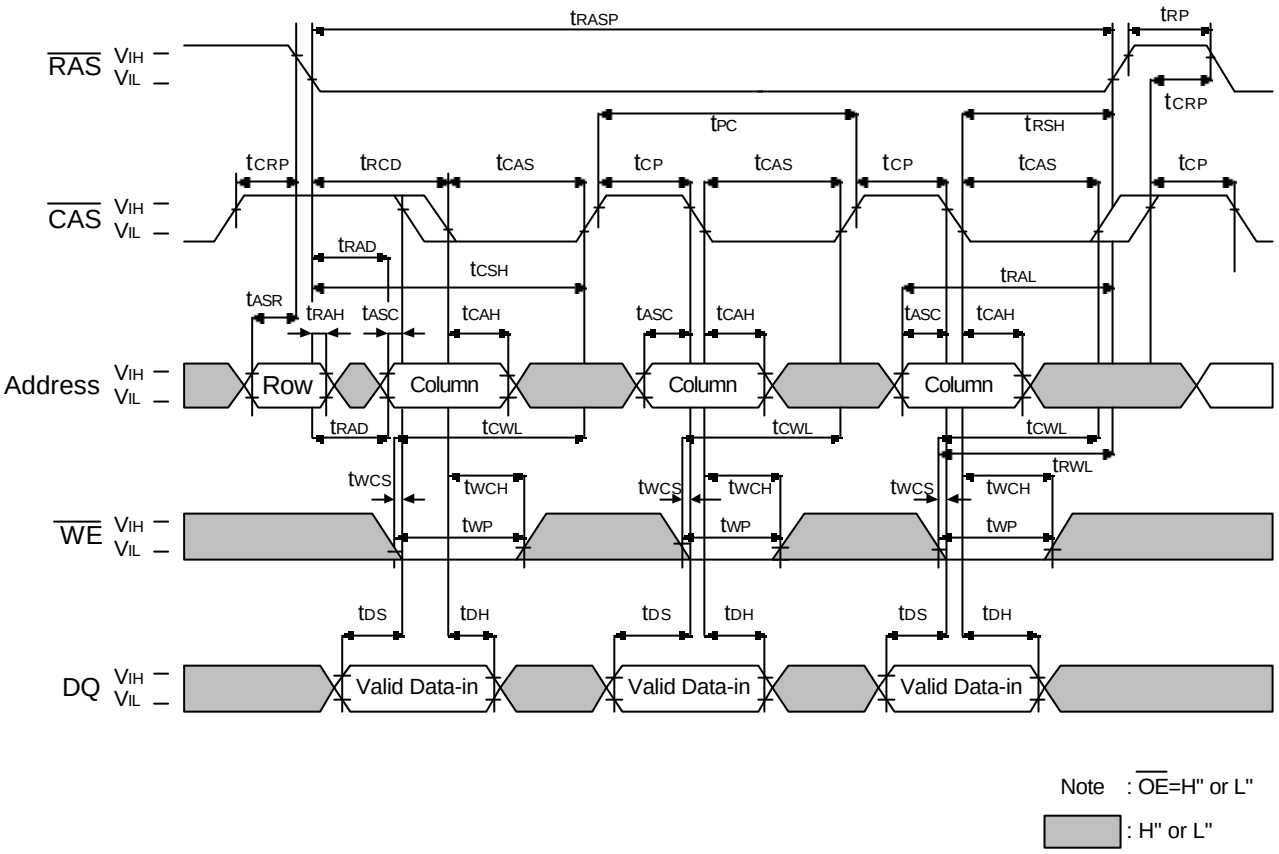
Read Modify Write Cycle



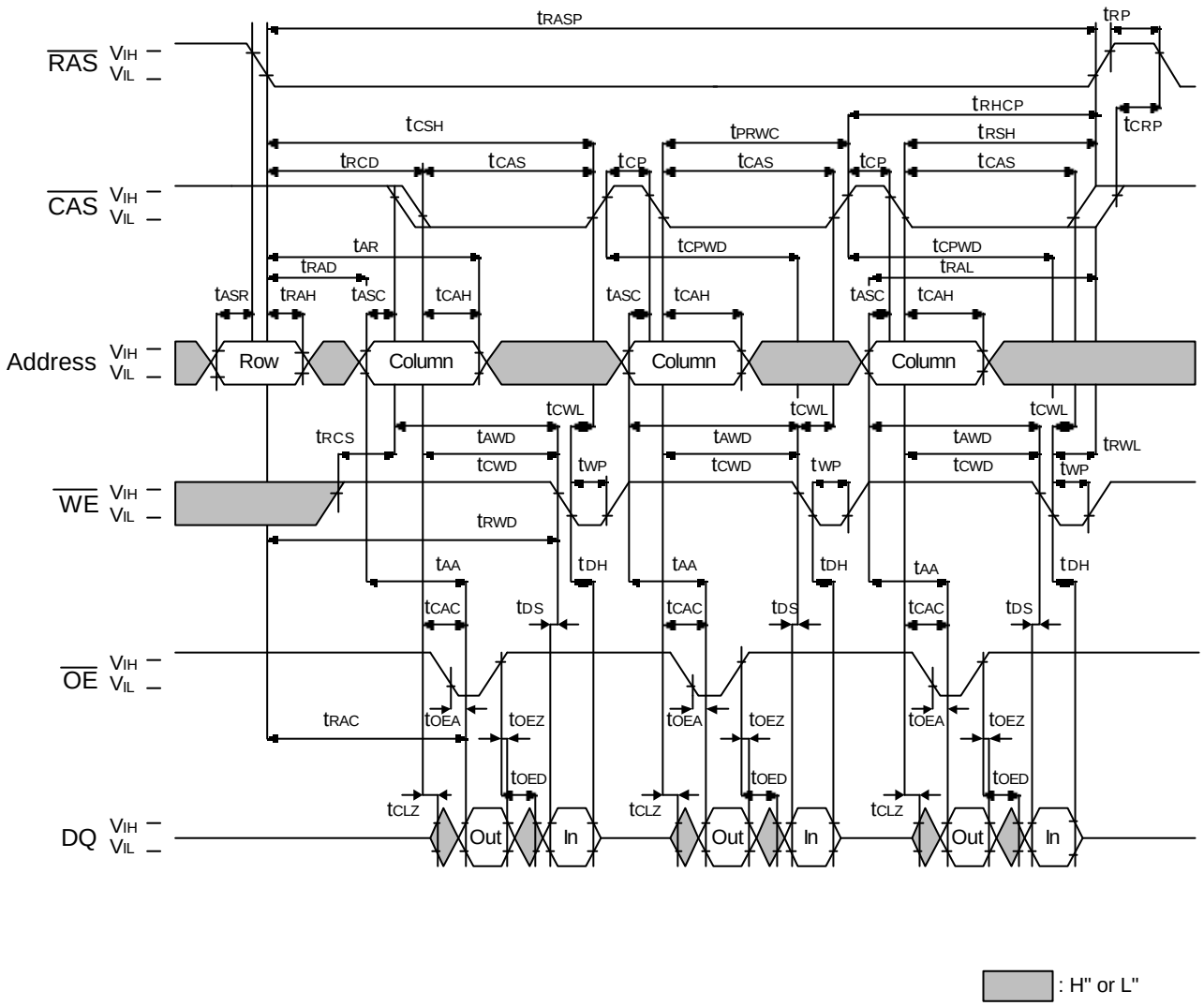
Fast Page Mode Read Cycle



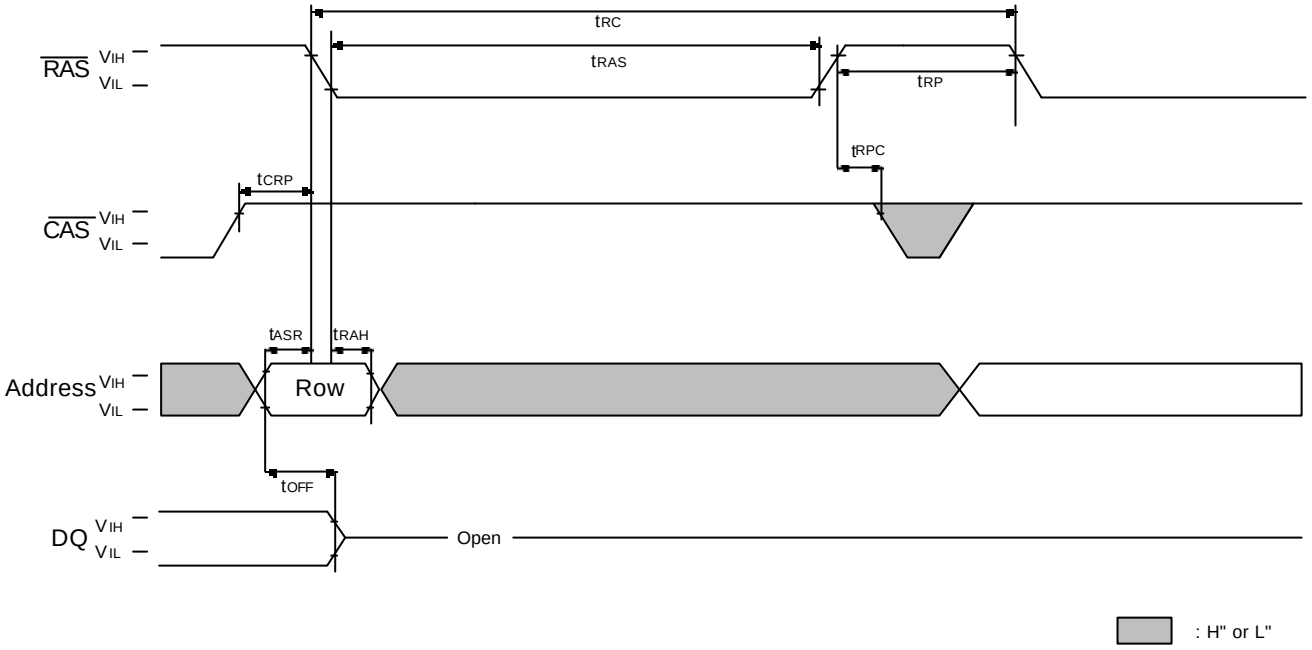
Fast Page Mode Write Cycle (Early Write)



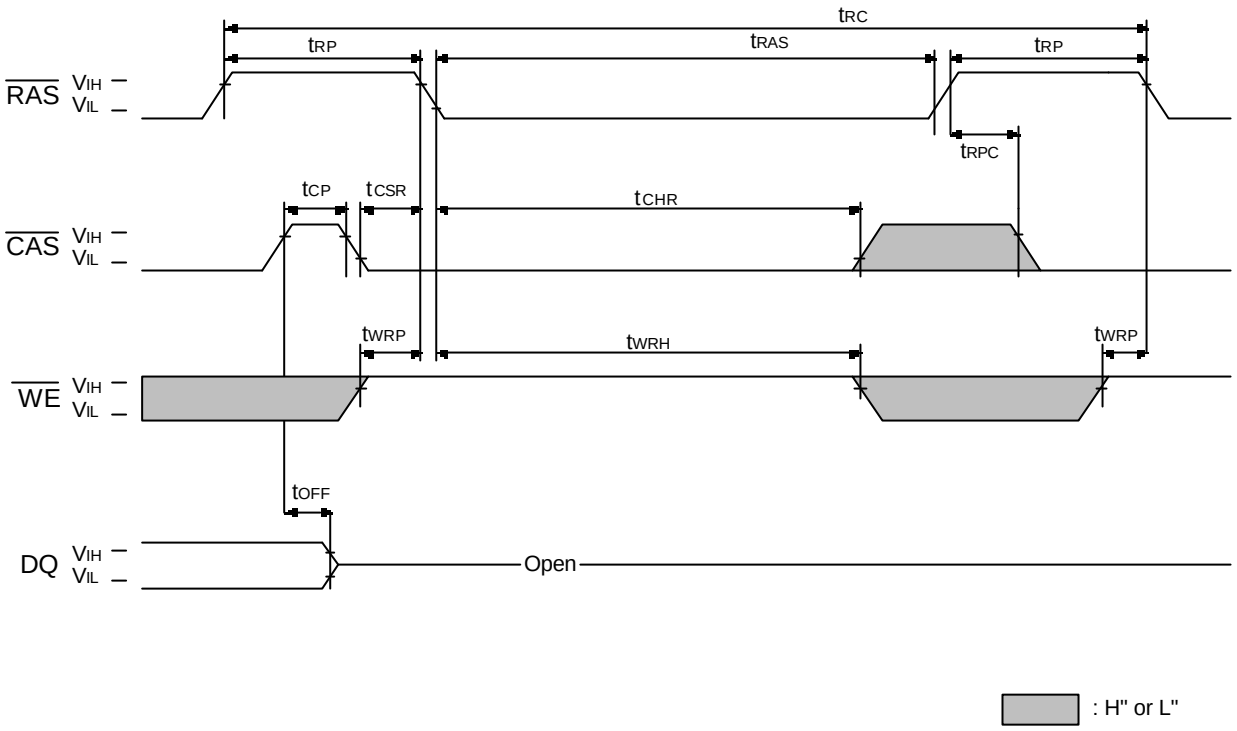
Fast Page Mode Modify Write Cycle



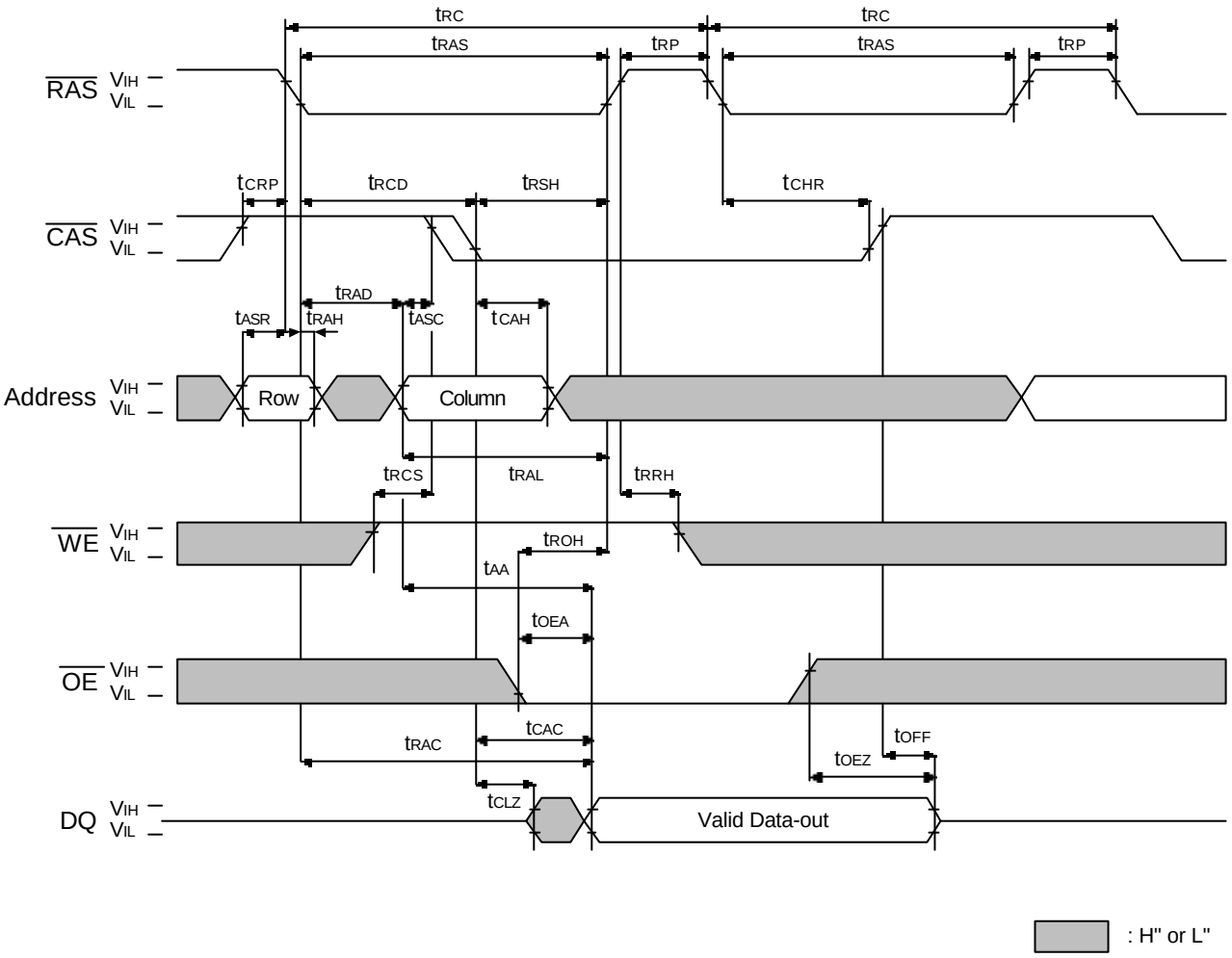
RAS-Only Refresh Cycle



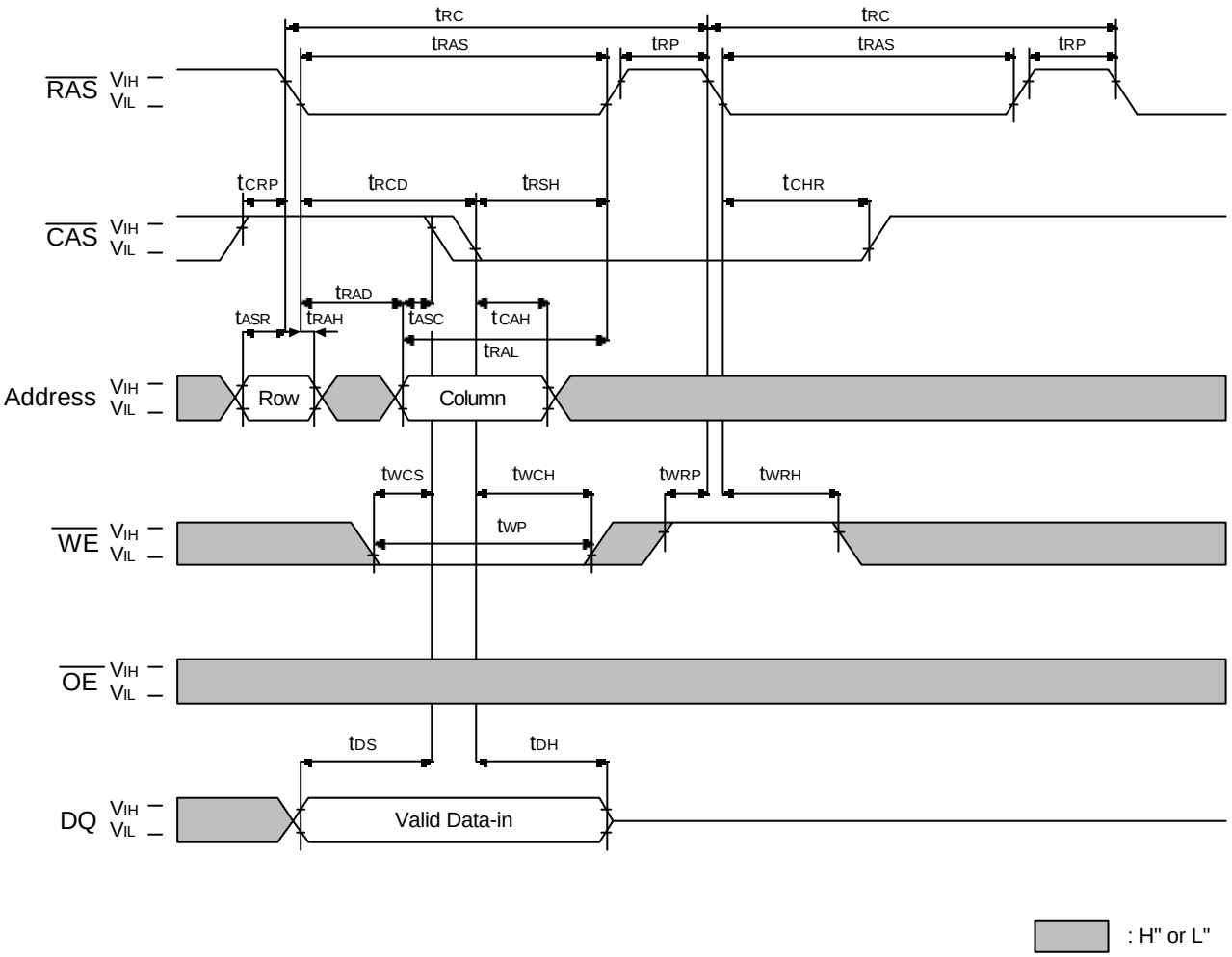
CAS-before-RAS Refresh Cycle



Hidden Refresh Read Cycle

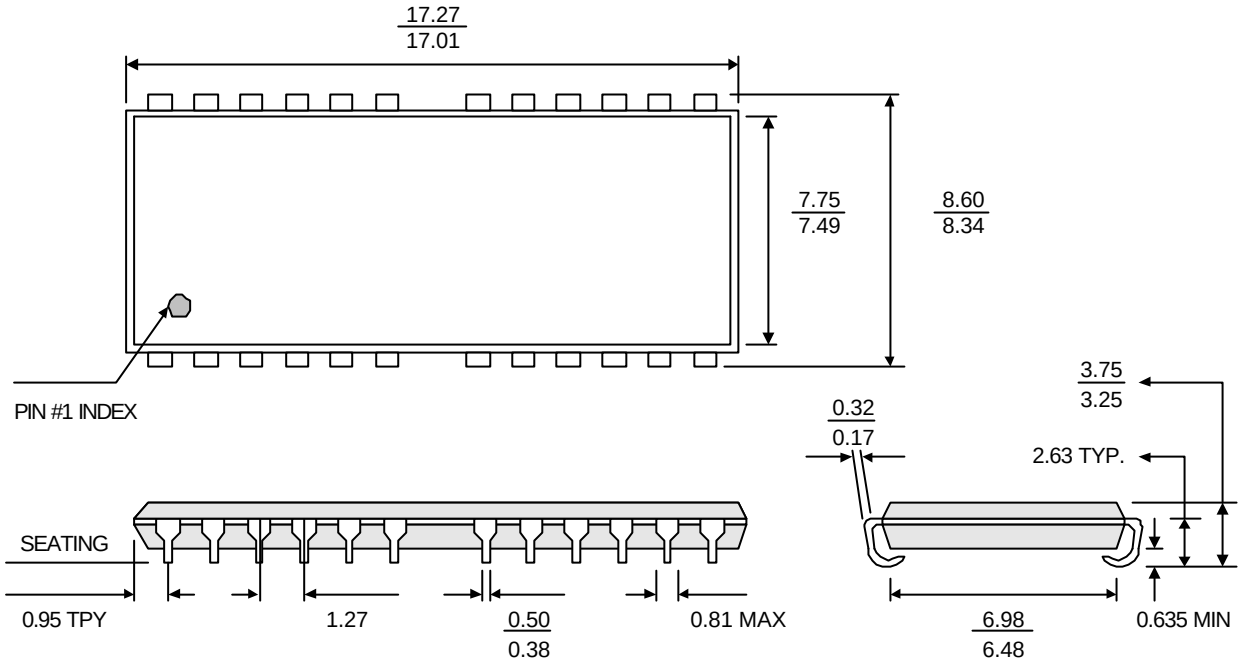


Hidden Refresh Write Cycle



PACKAGE DIMENSION

24/26-PIN PLASTIC SOJ (300mil)



NOTE : All dimensions in millimeters $\frac{\text{MAX}}{\text{MIN}}$ or typical where noted.